



# MCH3414

## N-Channel Silicon MOSFET

### General-Purpose Switching Device Applications

#### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

#### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		1	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	0.8	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.5A	0.45	0.9		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =10V		480	630	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =4V		640	900	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		70		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		9.0		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		6.5		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		5		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		4		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		12		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		12		ns

Marking : KP

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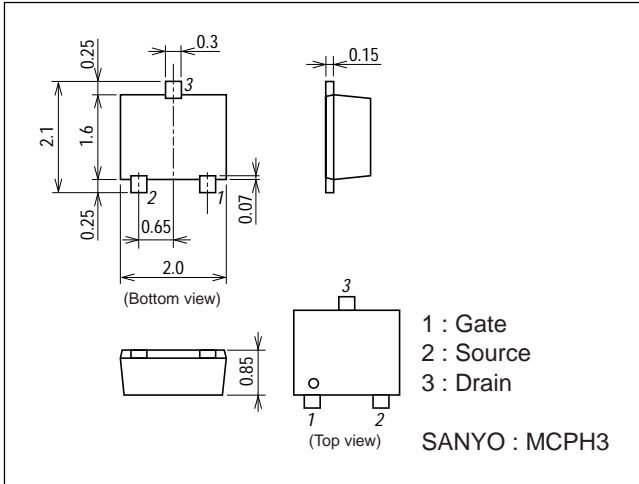
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A		3.0		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A		0.6		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A		0.6		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0		0.9	1.2	V

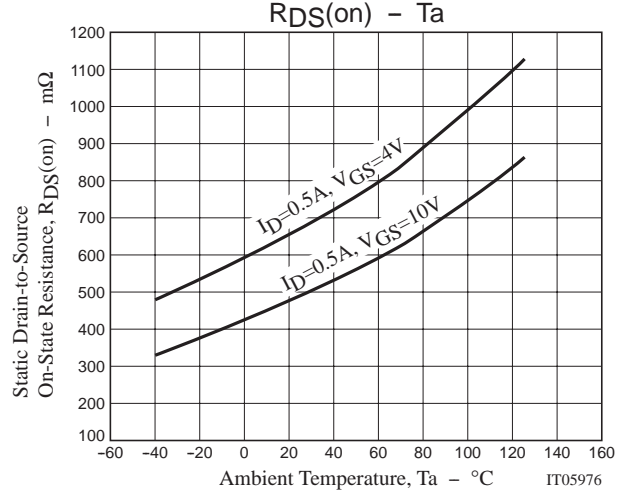
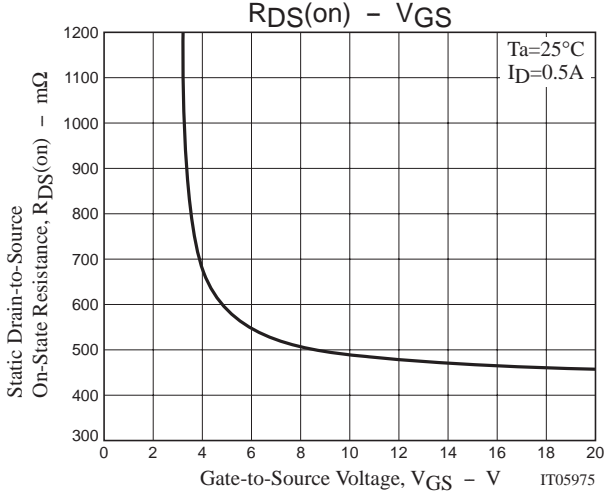
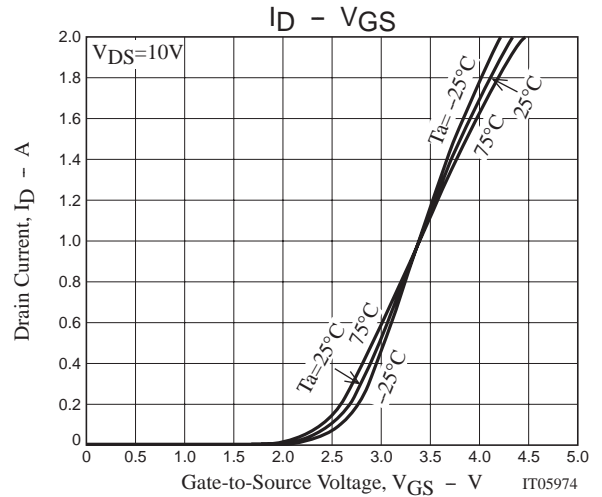
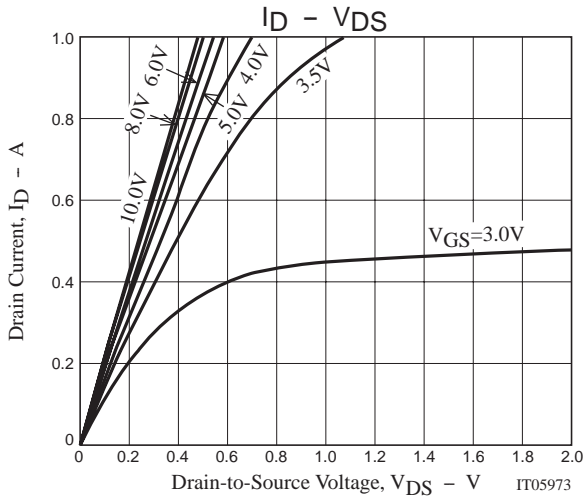
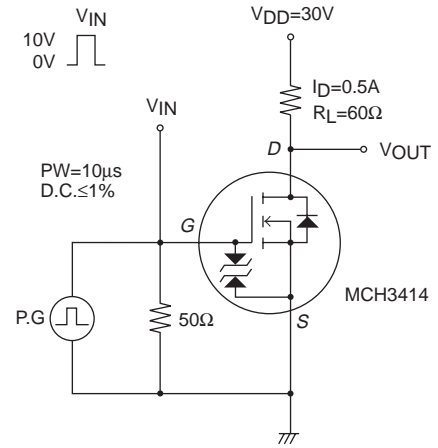
## Package Dimensions

unit : mm

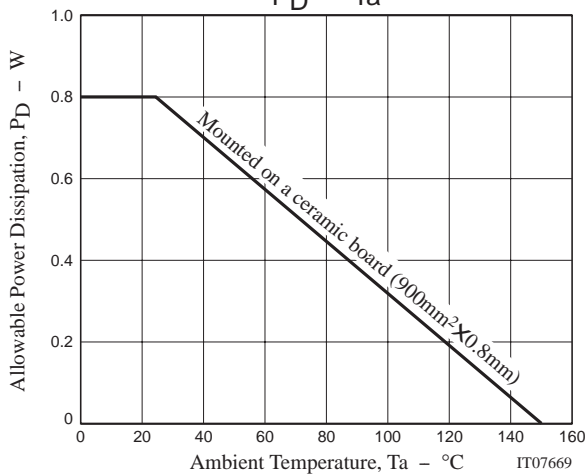
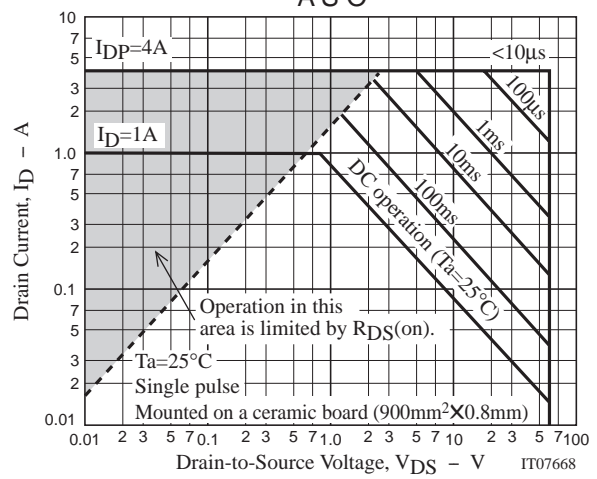
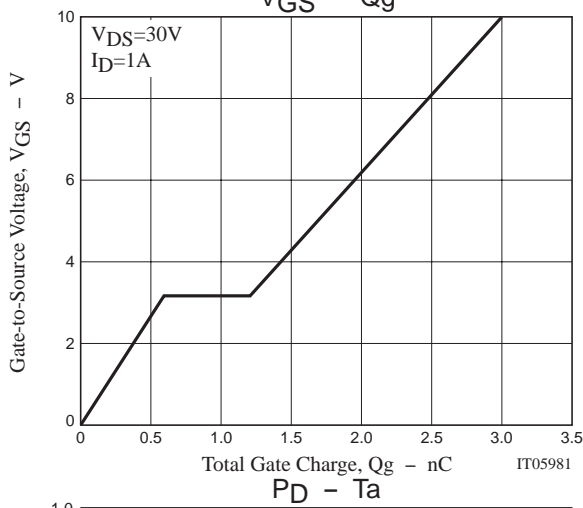
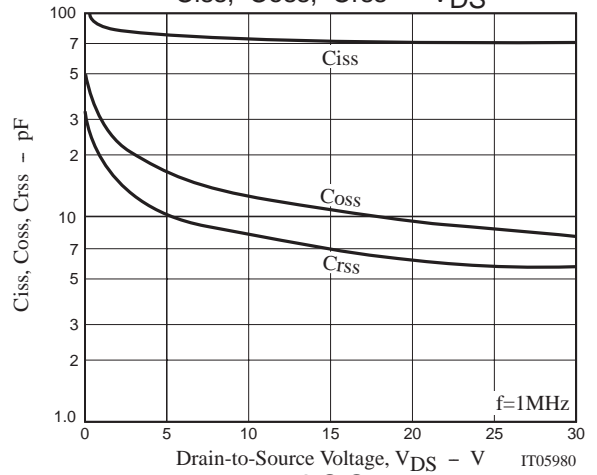
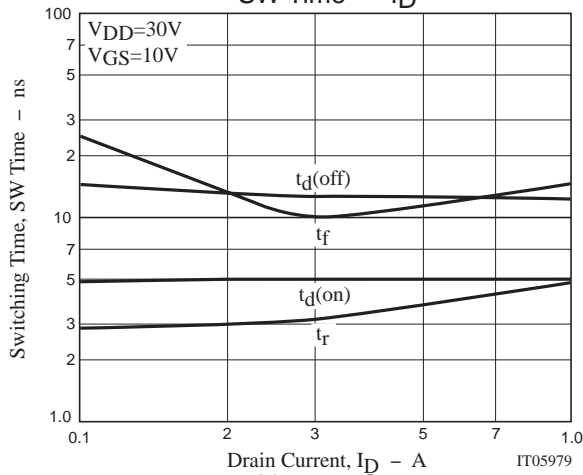
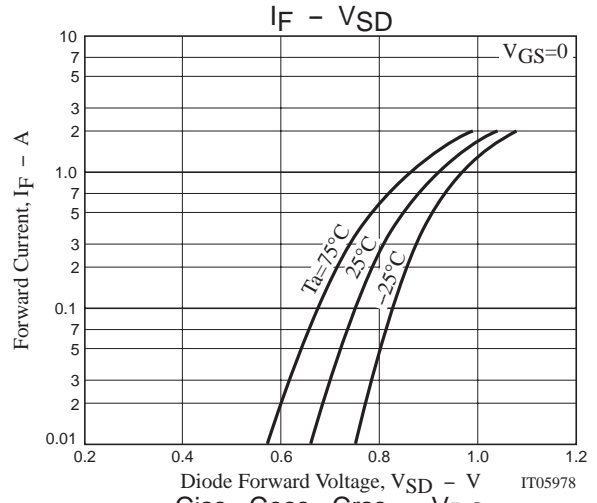
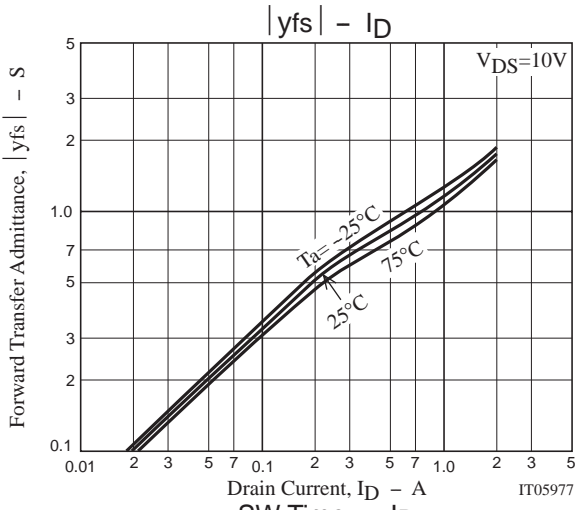
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## Switching Time Test Circuit



# MCH3414



Note on usage : Since the MCH3414 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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